

Flexible illumination for ultra-fine resolution with 0.33 NA EUV lithography



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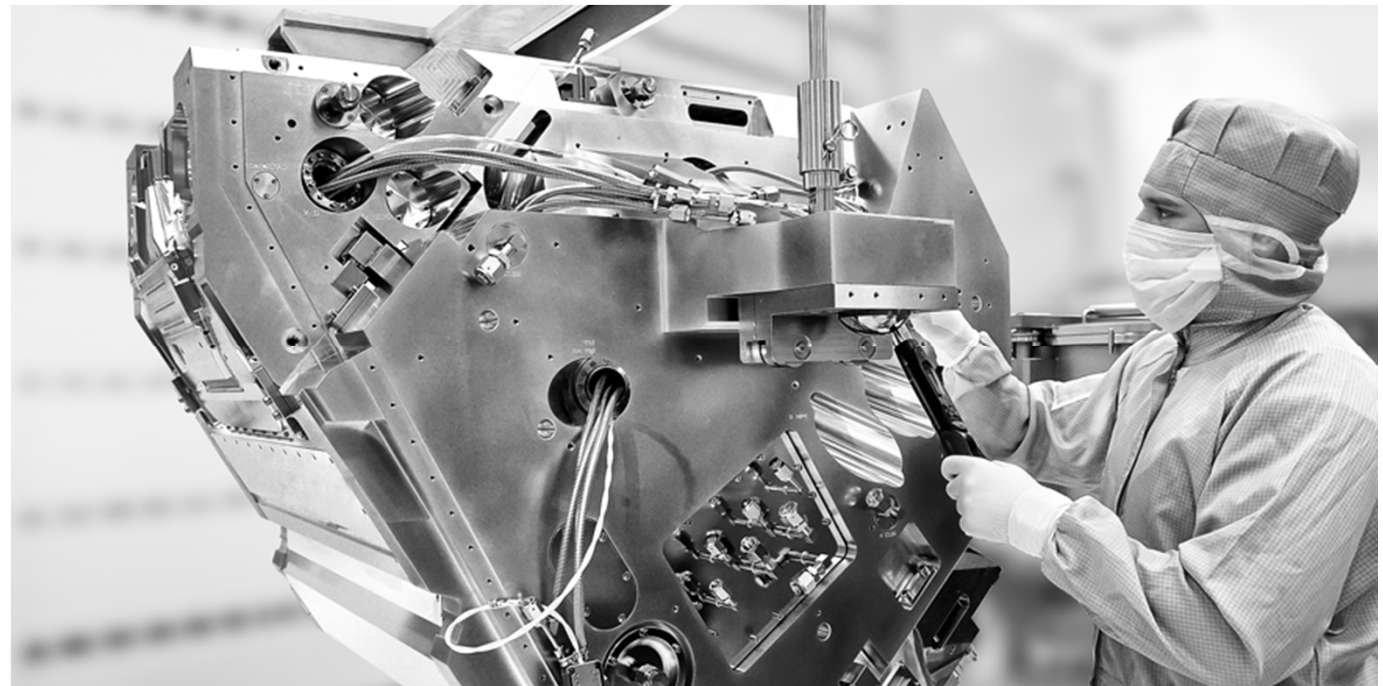
Alexander Winkler

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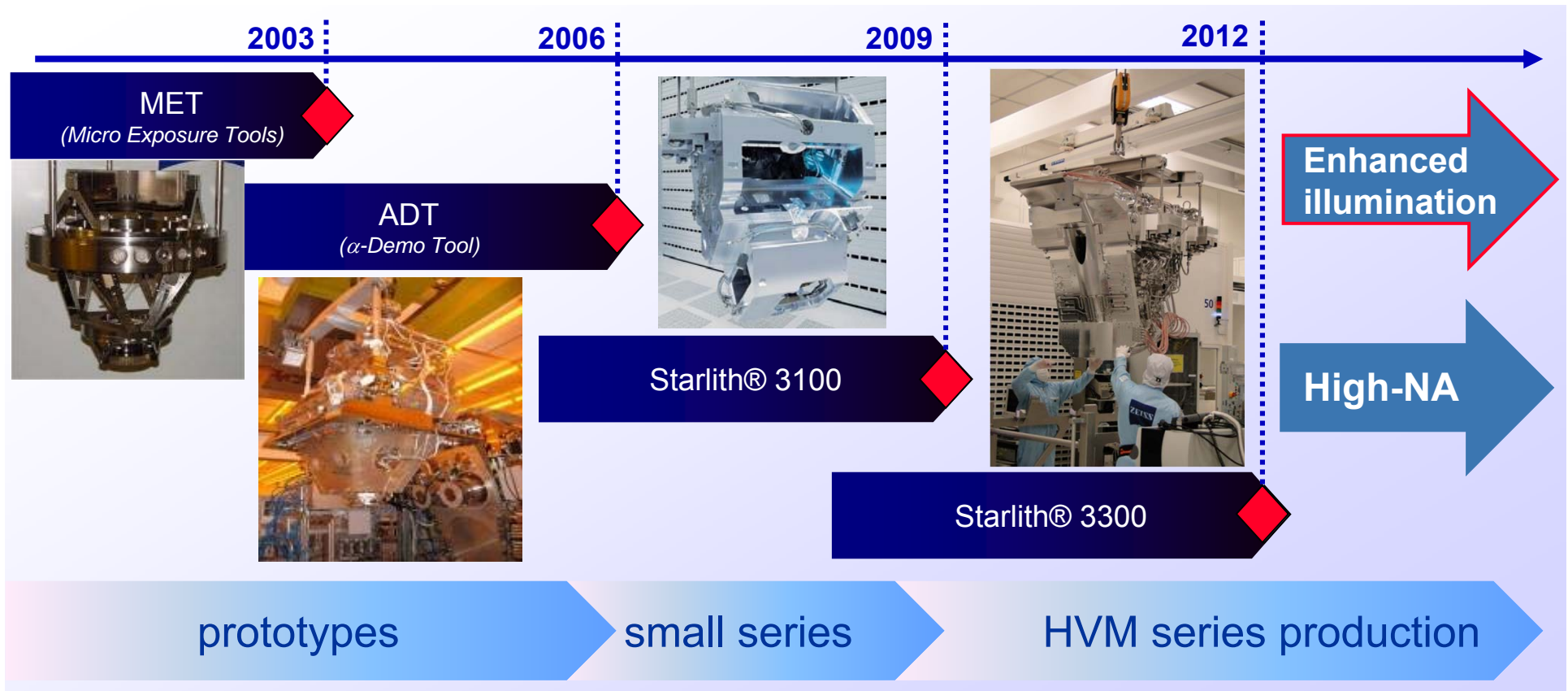
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ASML Brion



2016 International Symposium on Extreme Ultraviolet Lithography, Hiroshima, Japan, 2016-10-24

EUV program at ZEISS



Resolution enhancement by low-k1 illumination



$$\text{Resolution} = k_1 \cdot \frac{\lambda}{NA}$$

$\lambda = 13.5 \text{ nm}$
 $NA = 0.33$

A green circle highlights the k_1 term, with a green arrow pointing downwards towards the text below.



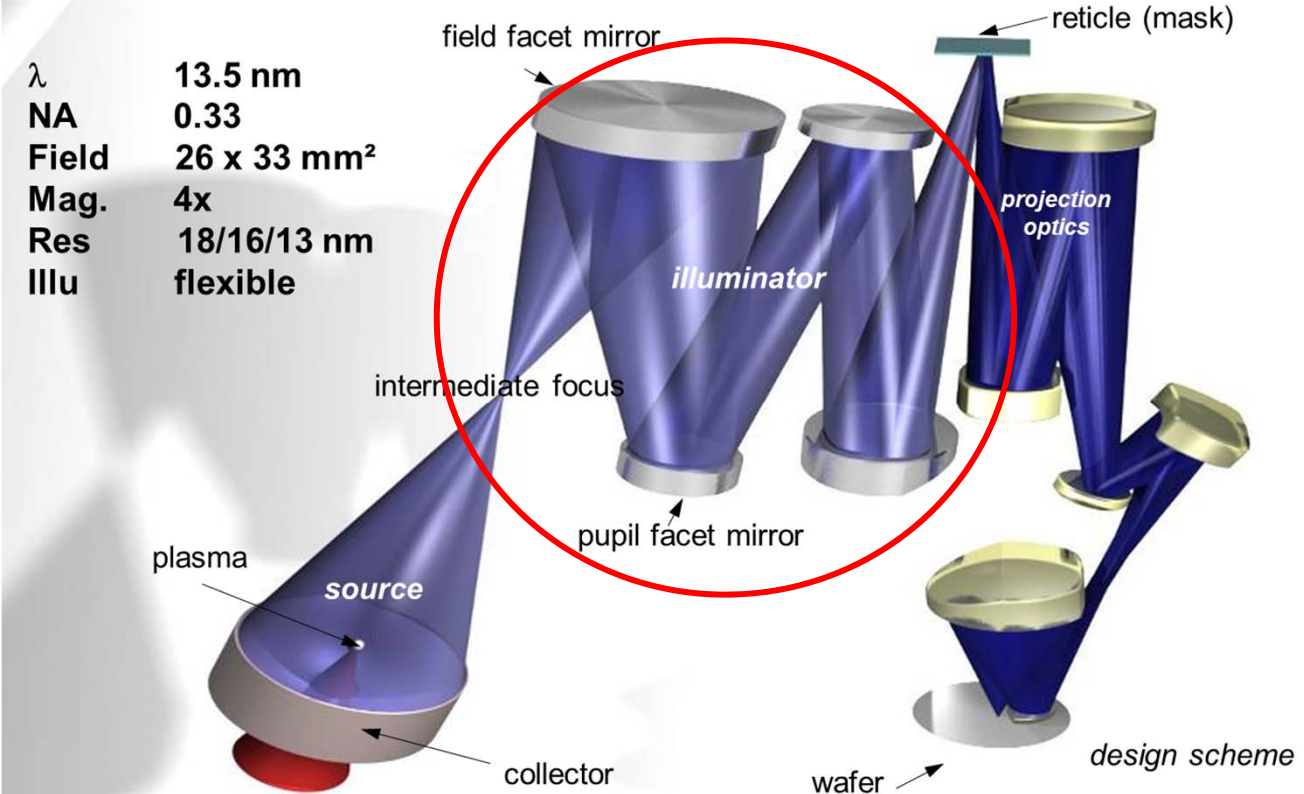
Ernst Abbe (1873)

Reduce the process factor k_1

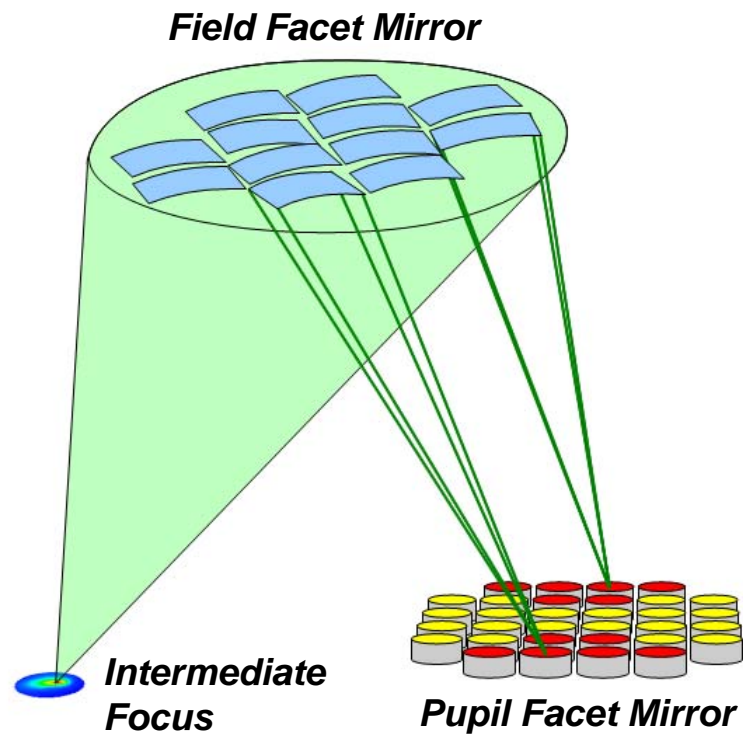
by applying enhanced **illumination** (similar as in DUV lithography)

- high sigma settings
- smaller pupil fill ratio
- customized freeform pupils

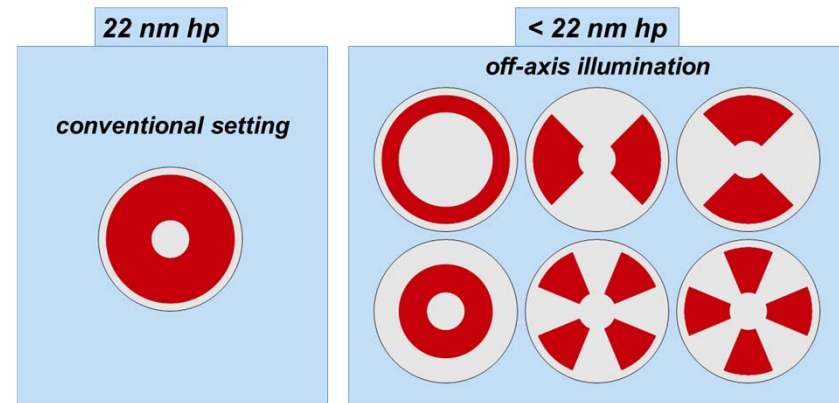
Starlith® 3300 optical train



Starlith® 3300 illuminator: Actuated fly's eye unit enables lossless setting changes



Standard pupil shapes



Pupil Fill Ratio (PFR) of EUV pupils

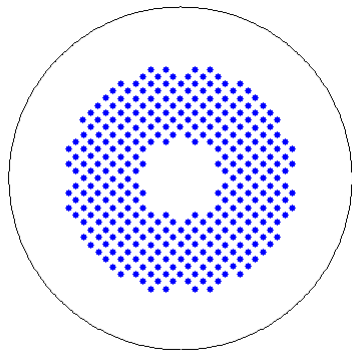


Pupil Fill Ratio (PFR) definition: the area of the pupil filled with energy

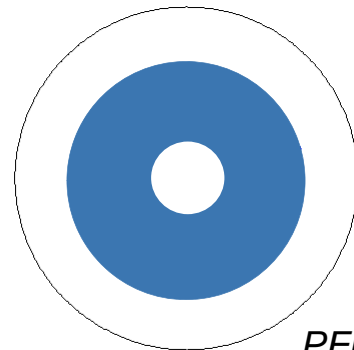
$$PFR = \frac{\sum_{n=1}^N I_n}{I_{\max} \cdot N}$$

N : number of grid pixels with $\sigma \leq 1$
 I_n : intensity of grid pixel n
 I_{\max} : max. intensity of any grid pixel

not applicable to discrete EUV pupils directly

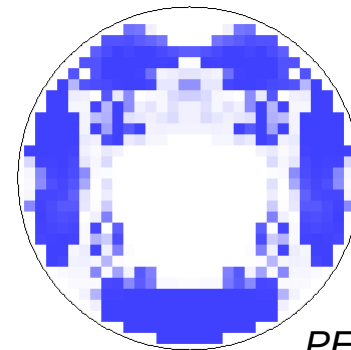


applicable to corresponding tophat envelope



$PFR = 40\%$

also applicable to greyscale freeforms



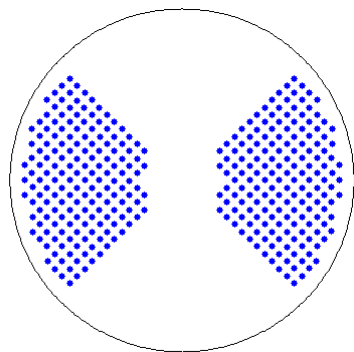
$PFR = 43\%$

Decrease the Pupil Fill Ratio (PFR) on the Starlith® 3300 illuminator

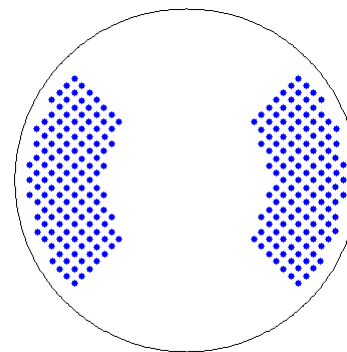


Pupil shapes with smaller PFR can be supported on the Starlith® 3300 illuminator, by switching off pupil channels, **reducing the illuminator efficiency**.

$$\text{illuminator efficiency} = \frac{\text{total energy which is used in the actual pupil}}{\text{total energy in the pupil if all channels were switched on}}$$



illuminator efficiency = 100%

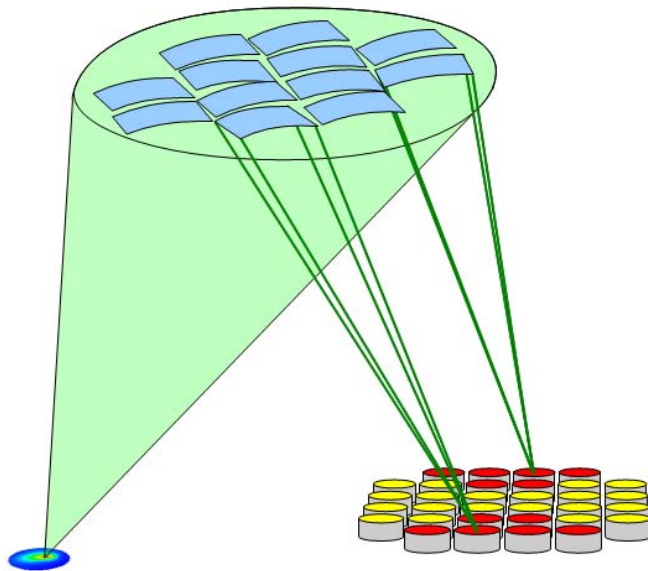


illuminator efficiency = 78%

Higher pupil flexibility by increased number of pupil facets



Pupil switching mechanism



Starlith® 3300:

one field facet can address two pupil channels

New generation:

one field facet can address many pupil channels

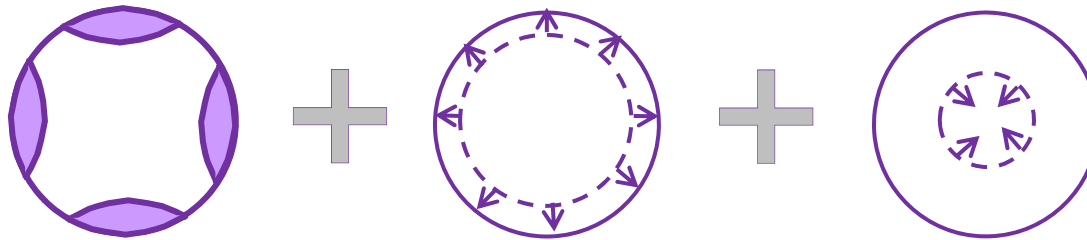
- decrease pupil filling
- enable $\geq 20\%$ pupil fill ratio at full illuminator efficiency

New generation illumination for low-k1 imaging

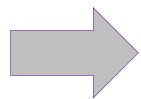


Decrease pupil filling

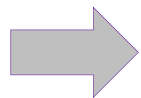
Extend sigma range



Optimized pole shapes & maximum pupil flexibility



Highest possible resolution down to 13 nm with $NA = 0.33$ and $k_1 = 0.32$

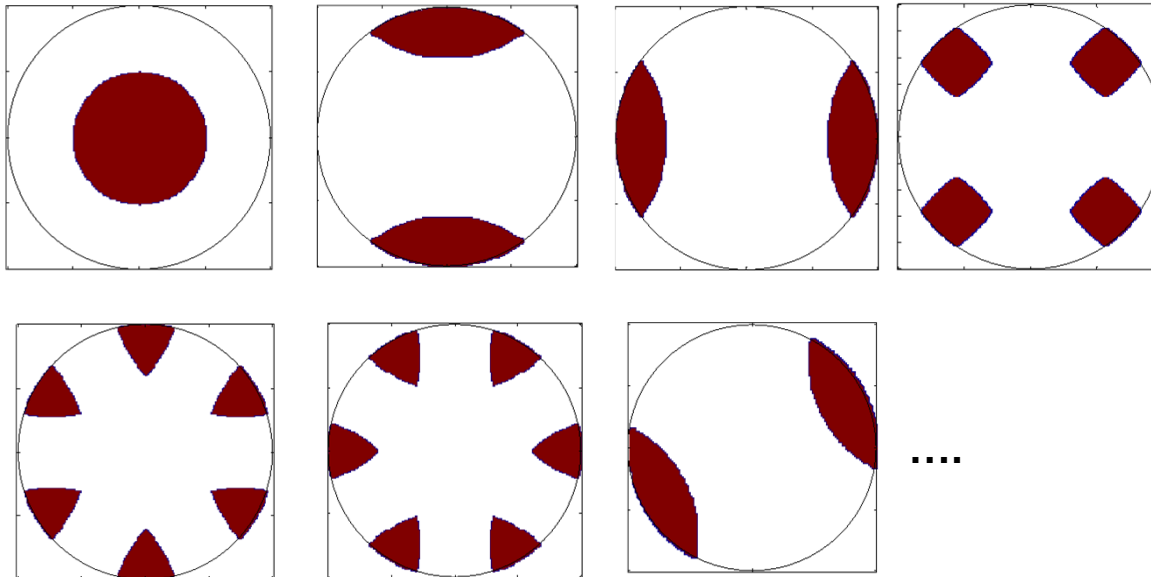


New & more illumination settings for upcoming nodes at full throughput

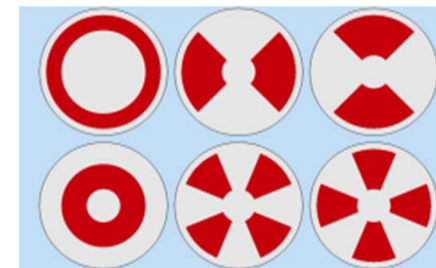
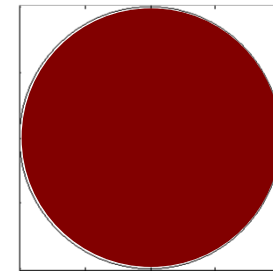
New generation pupil shapes



Pupil shapes with 20% pupil fill ratio



... and with larger pupil fill ratio

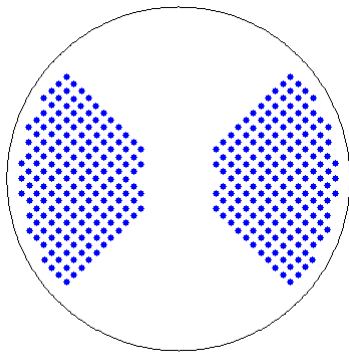


standard settings 3300

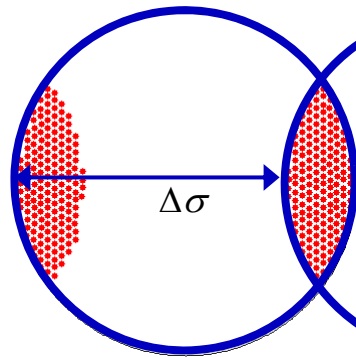
Leafshape Dipoles for 13 nm half-pitch resolution at 100% illuminator efficiency



Starlith® 3300



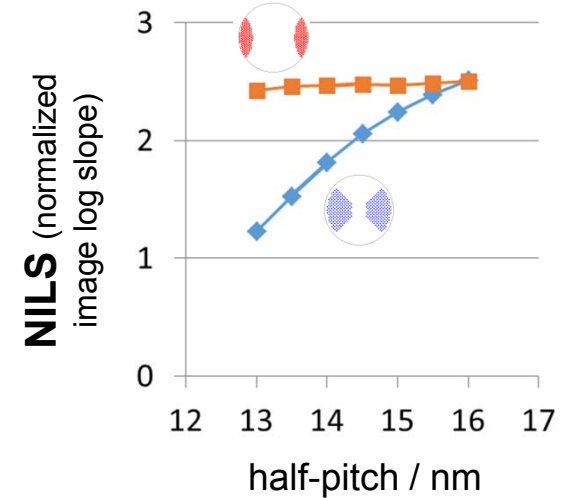
New generation



$$\Delta\sigma = \frac{\lambda}{NA \cdot p} = \frac{13.5 \text{ nm}}{0.33 \cdot 26 \text{ nm}} = 1.57$$

≈ 20% pupil fill ratio

aerial image simulation
(zero defocus, topographic mask)

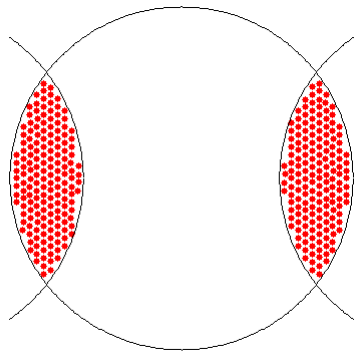


→ 13 nm resolution at full throughput

Dipoles for 13 nm half-pitch resolution Quasar for 18 nm half-pitch H & V

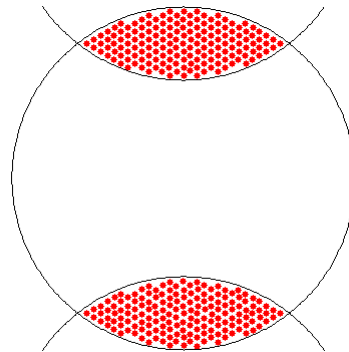


Dipole X



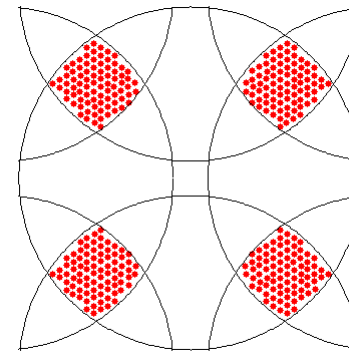
vertical Lines&Spaces
13 nm half-pitch

Dipole Y

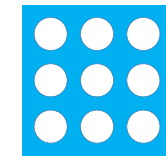


horizontal Lines&Spaces
13 nm half-pitch

Quasar



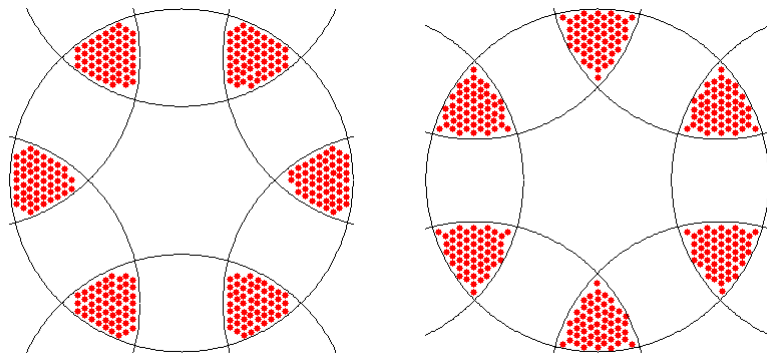
H&V Lines&Spaces Contact Hole array
18 nm half-pitch 18 nm half-pitch



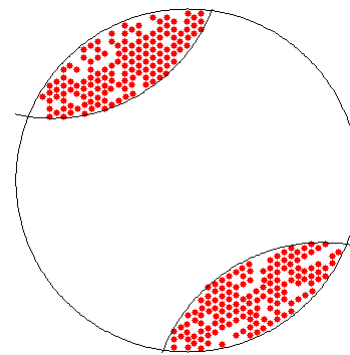
Hexapoles and Rotated Dipoles for DRAM



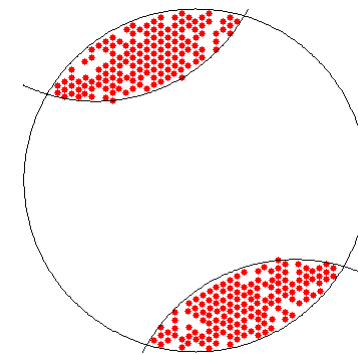
Hexapoles



Rotated Dipoles 30°

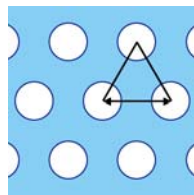


Rotated Dipoles 22°

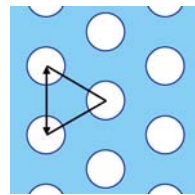


for DRAM storage node (hexagonal contact hole array)

16.5 nm half-pitch Single Exposure

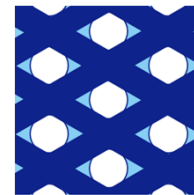


15 nm hp Double Patterning



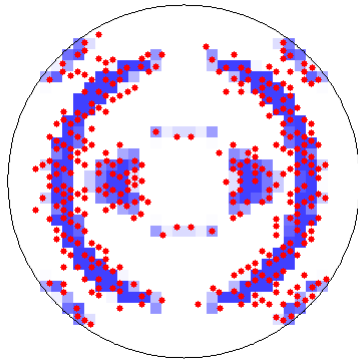
for DRAM active area

13 nm hp SE

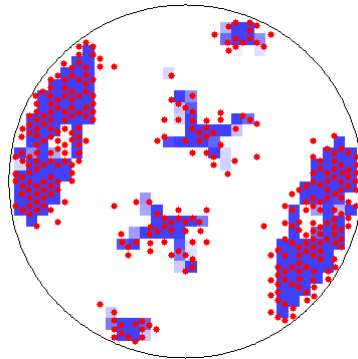


Freeform pupil shapes

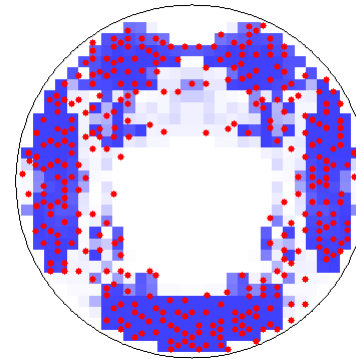
SMO pupil
for logic cut mask



rotated pupil shape
for DRAM brickwalls



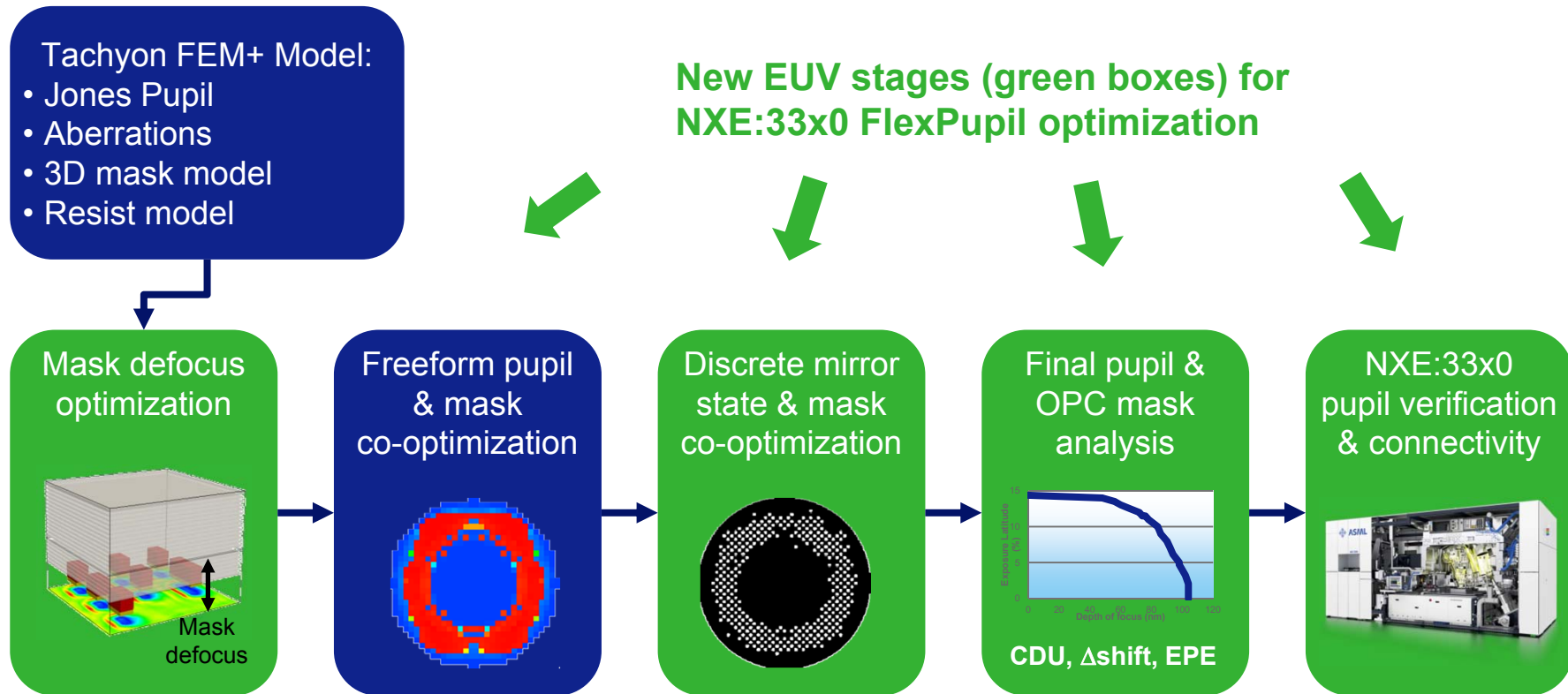
y-asymmetric
3D mask compensation



■ target shape
● EUV pupil

all examples without light loss (100% illuminator efficiency) on
new generation illumination system

Source mask optimization (SMO): Tachyon SMO NXE flow



Pupil properties taken into account in Tachyon SMO NXE flow



to achieve best match of optimized freeform pupil to final EUV pupil:

- min/max sigma range of illuminator generation
- minimum pupil fill ratio for lossless pupil (i.e. **100% illuminator efficiency**)

3300: min **PFR** \approx 40%

new generation: min **PFR** \geq 20%

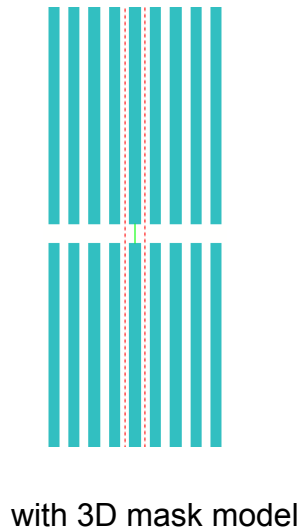
ZEISS models integrated into Tachyon SMO NXE flow



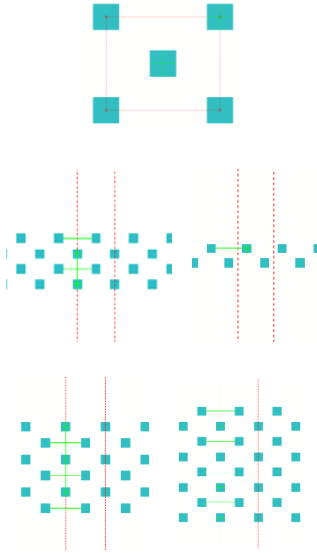
ZEISS pupil prediction model integrated into Tachyon SMO flow

→ Tachyon SMO results can make use of illumination properties most effectively

Tip-to-tip pattern: 13 nm half-pitch, 24 nm gap

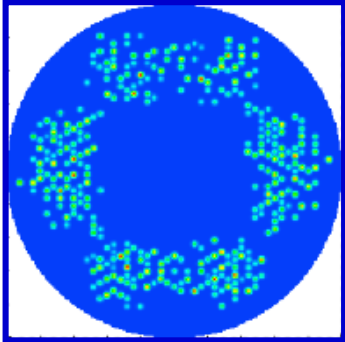
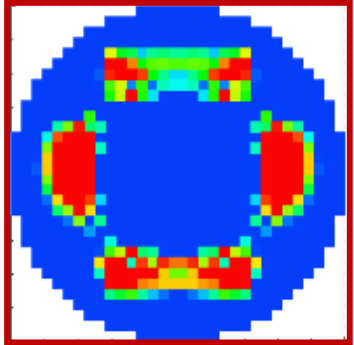
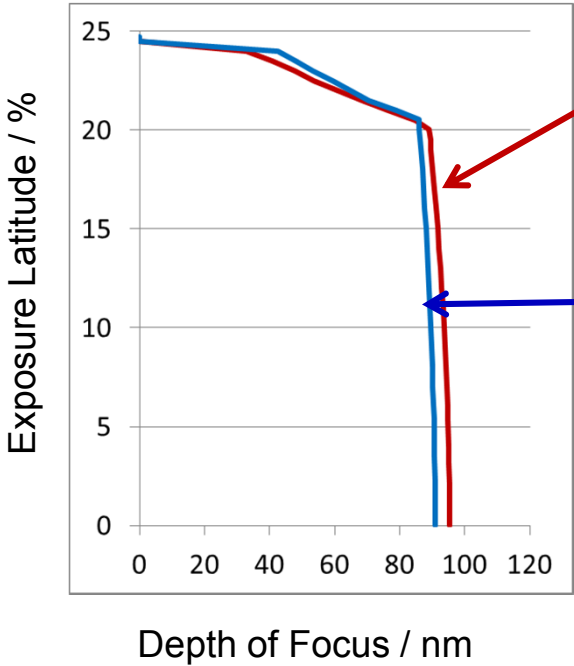


Via array: 20 nm squares, 42 nm min. pitch



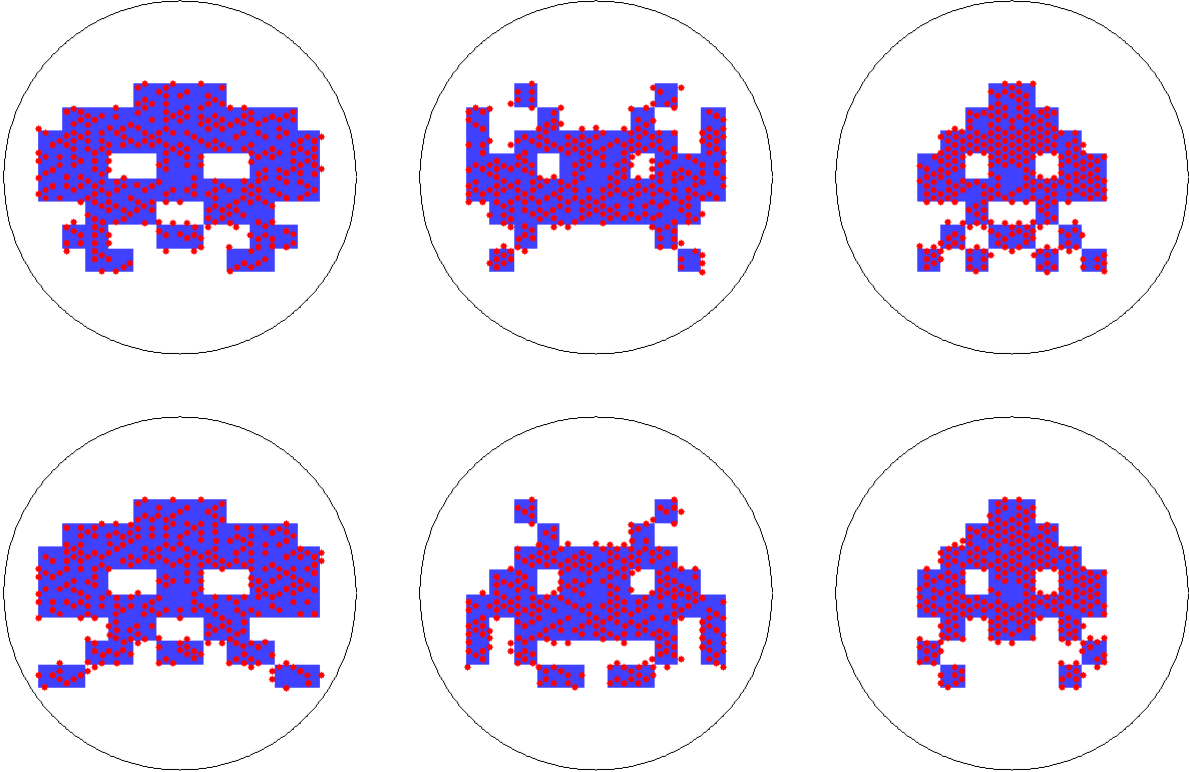
with 3D mask model

Process window



→ Process window of freeform pupil is maintained by EUV pupil. (100% illuminator efficiency)

Arbitrary freeform pupil shapes are possible



■ target shape
● EUV pupil

Shapes designed by Tomohiro Nishikado (1978)

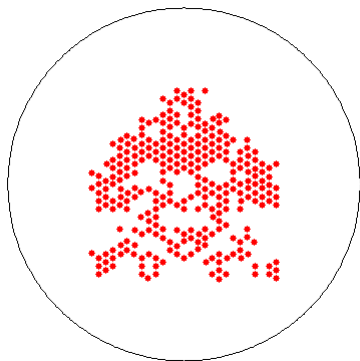
Pupil tuning can adjust proximity bias



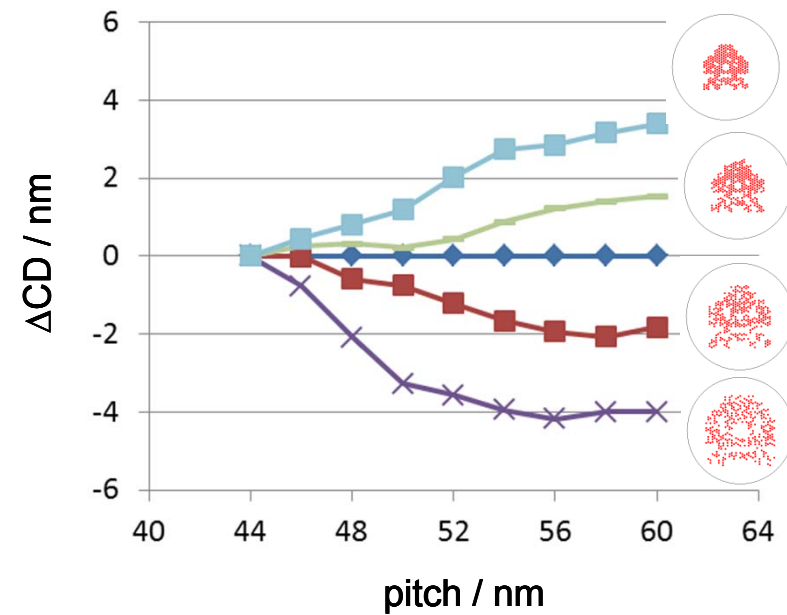
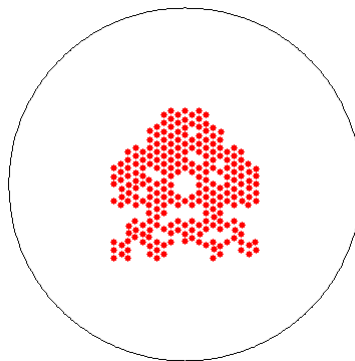
after mask tape-out, tweak the process to adjust the proximity curve, i.e. iso-dense bias?

→ adjust the pupil by switching a few pupil spots

original pupil



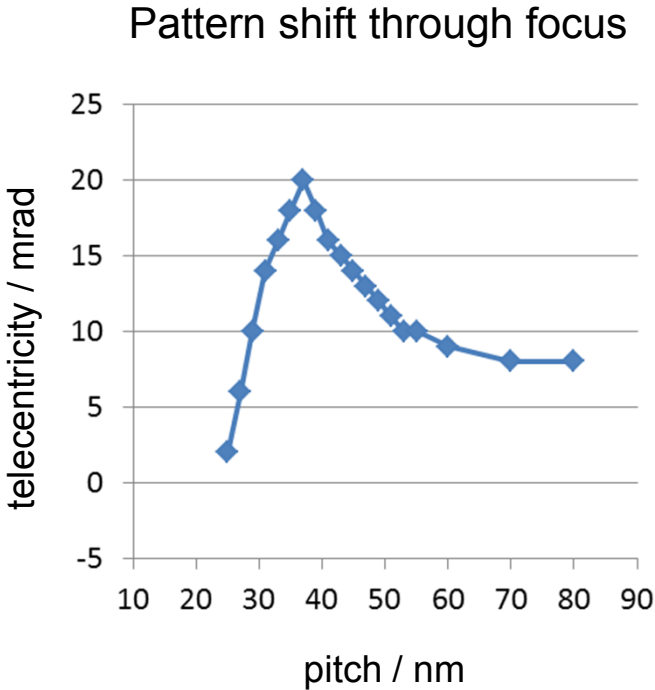
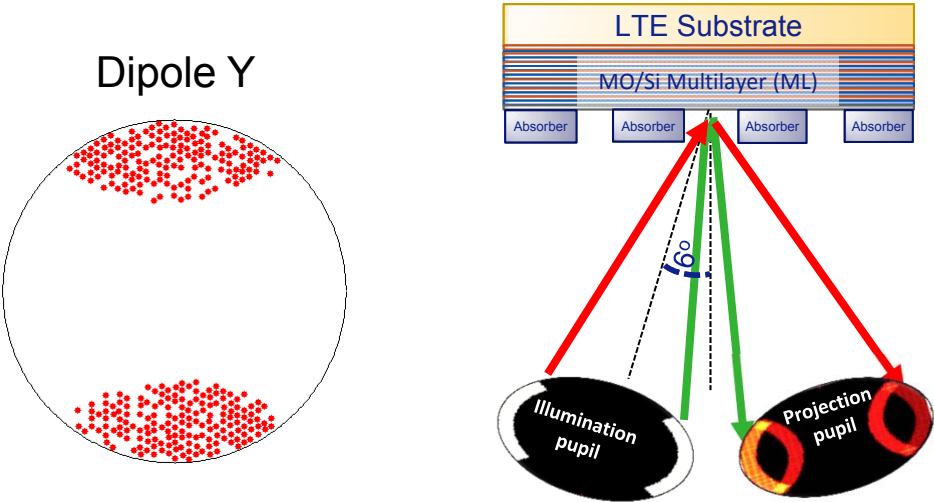
after pupil tuning



Another challenge for pupil tuning: 3D mask induced pattern shift through focus



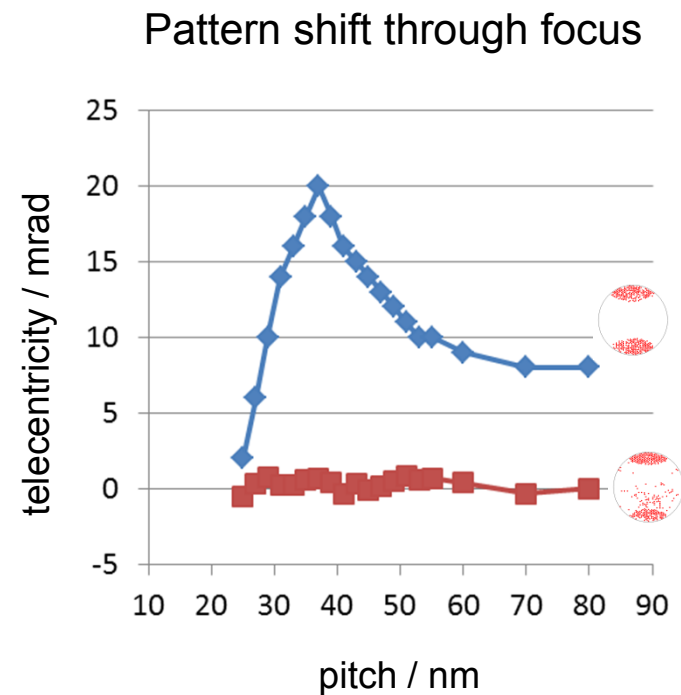
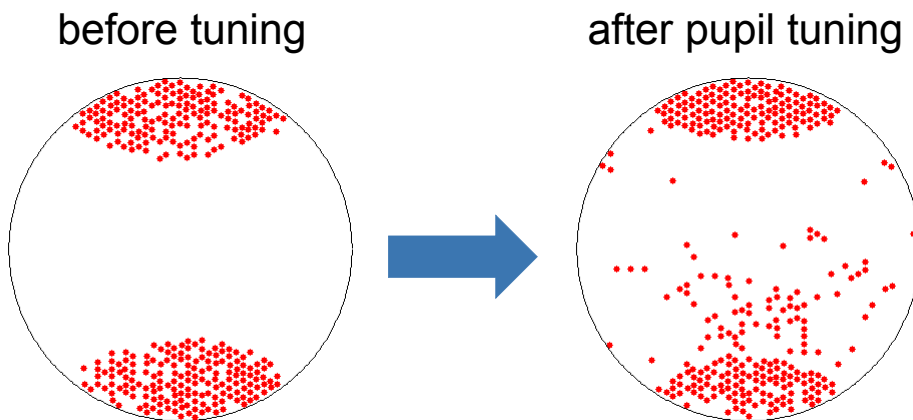
due to oblique incidence on mask,
3D mask effect can induce imaging telecentricity
(placement error divided by defocus)



Pupil tuning can compensate for 3D mask induced pattern shift through focus



→ adjust the pupil (induce a pupil imbalance) to compensate for the 3D mask induced telecentricity through pitch (while maintaining the proximity behavior)



Summary: Flexible illumination at 0.33 NA



- New generation EUVL illumination will support 20% pupil fill ratio (PFR) at full illuminator efficiency, and cover the full sigma range.
- Will provide lossless pupil shapes for ultimate imaging resolution for 0.33 NA EUVL at 13 nm half-pitch, or bi-directional imaging at 18 nm half-pitch H&V.
- High pupil flexibility ensures support of Source Mask Optimization (SMO).
 - can generate arbitrary customized freeform pupils with $\geq 20\%$ pupil fill ratio.
 - Predictive illuminator model is integrated in Tachyon SMO software.
- High pupil flexibility supports pupil matching and Pupil Tuning applications.

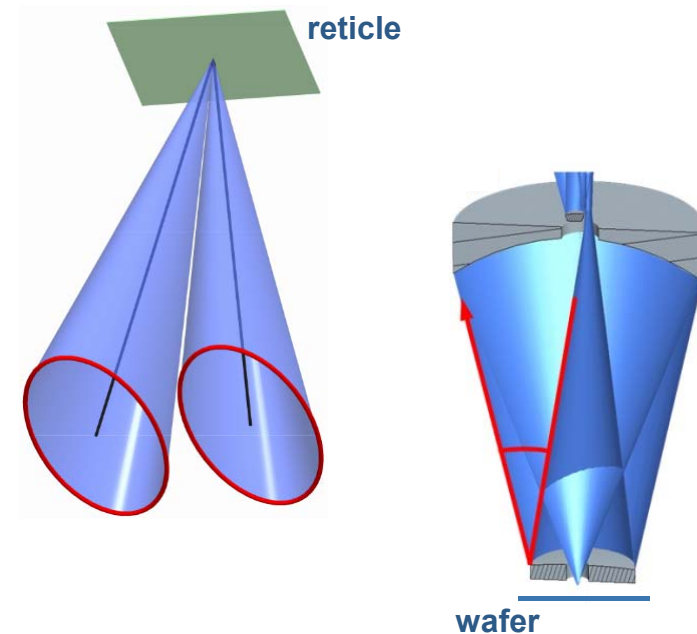
The roadmap continues: High NA



High NA EUVL will enable further shrink below 8 nm resolution.

High NA EUVL from illuminator perspective:

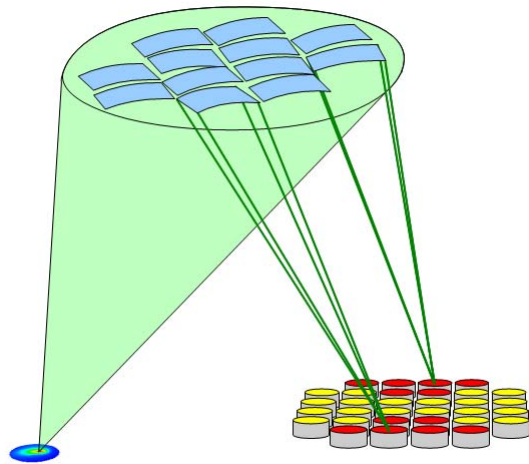
- larger angles
- anamorphic system
MAG 4x in x, MAG 8x in y
Angular cone of illumination light at reticle will be elliptical.
- central obscuration in the projection pupil



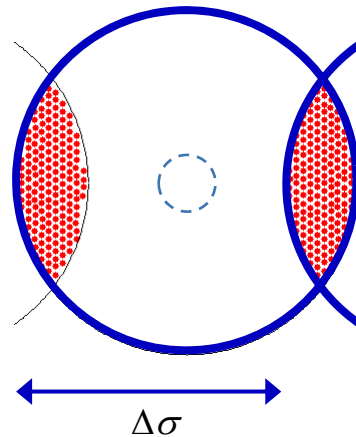
Flexible illumination for High NA



same Flex Pupil concept
can be used

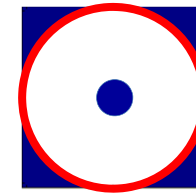


Dipole setting for
ultimate resolution



20% pupil fill ratio for
 ≤ 8 nm resolution

POB obscuration



not limiting the illumination
no need to put illumination
light into the pupil center

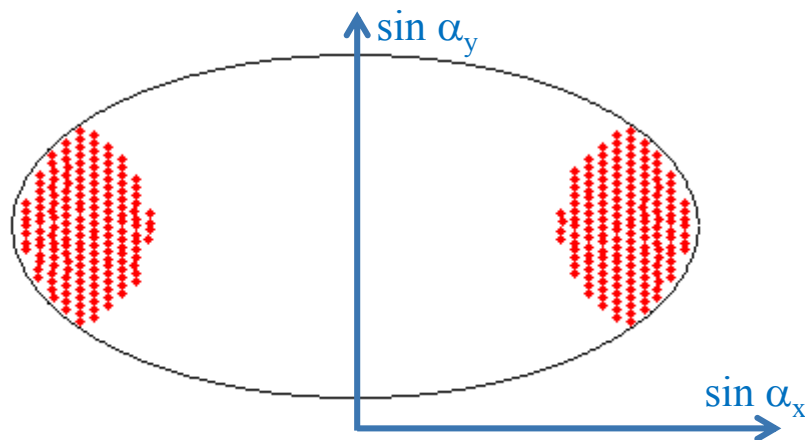
Flexible illumination for High NA



Anamorphic system:

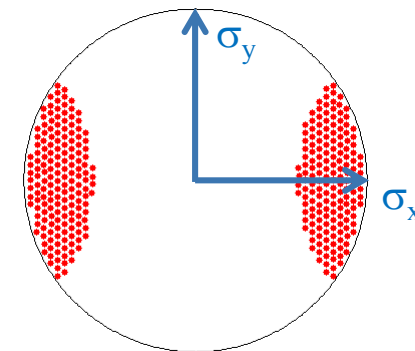
physical angles

- illumination pupil looks elliptical
- simulation SW takes the actual angles into account for 3D mask calculation



normalized pupil coordinates (“sigma”)

- pupil looks circular, by definition of sigma coordinates
- business as usual for lithographer



Conclusion



- **High pupil flexibility at 0.33 NA**

- will provide lossless pupil shapes for 13 nm half-pitch resolution.
- will provide arbitrary lossless pupils with $\geq 20\%$ PFR, for SMO and Pupil Tuning.
- Predictive illuminator model is integrated in Tachyon SMO software.

- **Extension to High NA EUVL**

- Flex illuminator concept can be extended to High NA anamorphic litho optics.
- will provide lossless pupil shapes for ≤ 8 nm half-pitch resolution and support SMO and Pupil Tuning applications.
- Low- k_1 EUVL for subsequent nodes will be enabled by flexible low-PFR illumination on high-NA EUVL systems.

Acknowledgements



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